

AMENDMENTS TO THE CLAIMS:

Please cancel claims 34 and 36, without prejudice or disclaimer of the subject matter thereof, and rewrite claim 37 in independent form as indicated below.

This listing of claims will replace all prior versions and listings of claims in the application:

1. (Previously Amended) A semiconductor device comprising:

a first conductor;

a first insulating film formed on said first conductor;

a second conductor including a first plug and a second plug formed on said first conductor through said first insulating film;

a third conductor including a first wire formed on said first insulating film and the first plug and a second wire formed on an extension line of the first wire on said first insulating film and the second plug; and

a second insulating film formed on said third conductor and over said first insulating film, said second insulating film including a thin area over said second conductor for guiding a laser beam.

2. (Previously Amended) The semiconductor device of claim 1, wherein:

said second conductor includes a third plug and a fourth plug formed on said first conductor through said first insulating film; and

FINNEGAN
HENDERSON
FARABOW
GARRETT &
DUNNER LLP

1300 I Street, NW
Washington, DC 20005
202.408.4000
Fax 202.408.4400
www.finnegan.com

said third conductor includes a third wire formed parallel with the first wire on said first insulating film and the third plug and a fourth wire formed on an extension line of the third wire on said first insulating film and the fourth plug.

3. (Canceled)

4. (Canceled)

5. (Previously Presented) The semiconductor device of claim 2, wherein:

said second conductor includes a fifth plug lined up on a first straight line with the first plug and the third plug on said first conductor through said first insulating film and a sixth plug lined up on a second straight line with the second plug and the fourth plug on said first conductor through said first insulating film.

6. (Original) The semiconductor device of claim 1, wherein:

the first conductor has a wire shape.

7. (Original) The semiconductor device of claim 6, wherein:

the first conductor is in contact with a plurality of the second conductors.

8. (Original) The semiconductor device of claim 6, wherein:

an end of the first conductor is in contact with the second conductor; and

the first conductor is in parallel with the third conductor.

FINNEGAN
HENDERSON
FARABOW
GARRETT &
DUNNER LLP

1300 I Street, NW
Washington, DC 20005
202.408.4000
Fax 202.408.4400
www.finnegan.com

9. (Original) The semiconductor device of claim 8, wherein:

the first conductor is just under the third conductor.

10. (Original) The semiconductor device of claim 8, wherein the first conductor is obliquely below the third conductor.

11. (Original) The semiconductor device of claim 1, wherein:

the first conductor is a semiconductor substrate.

12. (Original) The semiconductor device of claim 1, wherein:

the first conductor is set at a predetermined potential level.

13. (Original) The semiconductor device of claim 1, wherein:

the third conductor is set at a predetermined potential level.

14. (Original) The semiconductor device of claim 1, wherein:

the third conductor is mainly made of one of aluminum and copper.

15. (Original) The semiconductor device of claim 1, wherein:

the second conductor is mainly made of one of aluminum, tungsten, silicon, titanium, tantalum, and copper.

FINNEGAN
HENDERSON
FARABOW
GARRETT &
DUNNER LLP

1300 I Street, NW
Washington, DC 20005
202.408.4000
Fax 202.408.4400
www.finnegan.com

16. (Previously Presented) The semiconductor device of claim 1, wherein:

the second conductor includes a first portion formed on said first conductor and a second portion formed on the first portion made of different material from that of the first portion.

17. (Original) The semiconductor device of claim 1, wherein:

the first conductor is mainly made of one of aluminum, tungsten, silicon, titanium, tantalum, and copper.

18. (Original) The semiconductor device of claim 1, further comprising:

a fourth conductor formed under the first insulating film below the thin area;

a columnar fifth conductor having a bottom face that is in contact with a top face of the fourth conductor, the fifth conductor being formed below the thin area and passing through the first insulating film; and

a sixth conductor formed on the first insulating film under the second insulating film and separated from the fifth conductor, wherein:

the second insulating film has an opening above the fifth conductor.

19. (Original) The semiconductor device of claim 18, wherein:

the height of the fifth conductor is equal to the height of the second conductor.

20. (Original) The semiconductor device of claim 18, wherein:

the height of the fifth conductor is lower than the height of the second conductor.

FINNEGAN
HENDERSON
FARABOW
GARRETT &
DUNNER LLP

1300 I Street, NW
Washington, DC 20005
202.408.4000
Fax 202.408.4400
www.finnegan.com

21. (Original) The semiconductor device of claim 1, further comprising:
a fourth conductor formed under the first insulating film below the thin area; and
a sixth conductor formed on the first insulating film under the second insulating film and
separated from the fourth conductor, wherein:

the first insulating film has an opening on the fourth conductor below the thin area; and
the second insulating film has an opening above the opening of the first insulating film.

22. (Original) The semiconductor device of claim 21, wherein:
the opening of the first insulating film has taper angles that are small on the fourth
conductor side and large on the sixth conductor side.

23. (Original) The semiconductor device of claim 1, further comprising:
a fourth conductor formed under the first insulating film; and
a sixth conductor formed on the first insulating film under the second insulating film and
separated from the fourth conductor, wherein:

the first insulating film has an opening below the thin area; and
the second insulating film has an opening above the opening of the first insulating film.

24. (Withdrawn) A semiconductor integrated circuit comprising:
a latch circuit formed on a semiconductor substrate, for holding data corresponding to a
voltage applied to an input terminal thereof;

FINNEGAN
HENDERSON
FARABOW
GARRETT &
DUNNER ^{LLP}

1300 I Street, NW
Washington, DC 20005
202.408.4000
Fax 202.408.4400
www.finnegan.com

a first fuse formed on the semiconductor substrate and having a first terminal connected to the input terminal of the latch circuit, the first fuse being blown if irradiated with a laser beam; and

a second fuse formed on the semiconductor substrate under the first fuse and having a first terminal connected to a second terminal of the first fuse and a second terminal set at a predetermined voltage level.

25. (Withdrawn) The semiconductor integrated circuit of claim 24, further comprising:

a third fuse formed on the semiconductor substrate and having a first terminal connected to a second terminal of the second fuse and a second terminal connected to the latch circuit.

26. (Withdrawn) The semiconductor integrated circuit of claim 24, further comprising:

first memory cells formed on the semiconductor substrate;

second memory cells formed on the semiconductor substrate;

a first line formed on the semiconductor substrate and connected to the first memory cells;

a second line formed on the semiconductor substrate and connected to the second memory cells;

a decoder formed on the semiconductor substrate and having a first output terminal for providing a signal for selecting the first line and a second output terminal for providing a signal for selecting the second line;

a driver formed on the semiconductor substrate and having an input terminal connected to the first output terminal of the decoder, an output terminal connected to the first line, for

supplying a voltage to the first line according to the data stored in the latch circuit and the signal from the decoder; and

a replacement circuit formed on the semiconductor substrate and having an input terminal connected to the second output terminal of the decoder and an output terminal connected to the second line, to supply a voltage to the second line according to the data stored in the latch circuit and the signal from the decoder.

27. (Withdrawn) The semiconductor integrated circuit of claim 24, wherein:

the first fuse is mainly made of one of aluminum and copper.

28. (Withdrawn) The semiconductor integrated circuit of claim 24, wherein:

the second fuse is mainly made of one of aluminum, tungsten, silicon, titanium, tantalum, and copper.

29. (Withdrawn) A method of manufacturing a semiconductor device, comprising the steps of:

forming a first insulating film and a columnar second conductor on a first conductor;

forming a third conductor on the second conductor and first insulating film;

forming a second insulating film on the third conductor and first insulating film such that the second insulating film is thinned above the second conductor;

determining whether or not the first and second conductors must be disconnected from each other; and

FINNEGAN
HENDERSON
FARABOW
GARRETT &
DUNNER LLP

1300 I Street, NW
Washington, DC 20005
202.408.4000
Fax 202.408.4400
www.finnegan.com

emitting a laser beam toward a contact face between the first and second conductors when it is determined that the first and second conductors to be disconnected from each other.

30. (Previously Presented) A semiconductor device comprising:

a first insulating film;

a first lower wire formed on said first insulating film;

a second insulating film formed on said first lower wire;

a first conductor formed through said second insulating film including a first portion formed on said first lower wire and a second portion formed on the first portion made of a different material from that of the first portion;

a first upper wire formed parallel with said first lower wire on said second insulating film and said first conductor; and

a third insulating film formed on said first upper wire and over said second insulating film, said third insulating film including a thin area over said first conductor for guiding a laser beam.

31. (Previously Presented) The semiconductor device of claim 30, further comprising:

a second lower wire formed on an extension line of said first lower wire on said first insulating film beneath said second insulating film;

a second conductor formed through said second insulating film below the thin area including a third portion formed on said second lower wire made of a same material as the first portion and a fourth portion formed on the third portion made of a same material as the second portion; and

FINNEGAN
HENDERSON
FARABOW
GARRETT &
DUNNER LLP

1300 I Street, NW
Washington, DC 20005
202.408.4000
Fax 202.408.4400
www.finnegan.com

a second upper wire formed parallel with said second lower wire on said second insulating film and said second conductor beneath said third insulating film.

32. (Previously Presented) The semiconductor device of claim 30, wherein said first lower wire is obliquely below said first upper wire.

33. (Canceled)

34. (Canceled)

35. (Previously Presented) A semiconductor device comprising:

a semiconductor substrate;

a first insulating film formed on said semiconductor substrate;

a first conductor formed on said semiconductor substrate through said first insulating film, including a first portion formed on said semiconductor substrate and a second portion formed on the first portion made of different material from that of the first portion;

a first upper wire formed on said first insulating film and said first conductor; and

a second insulating film formed on said first upper wire and over said first insulating film, said second insulating film including a thin area over said first conductor for guiding a laser beam.

36. (Canceled)

FINNEGAN
HENDERSON
FARABOW
GARRETT &
DUNNER LLP

1300 I Street, NW
Washington, DC 20005
202.408.4000
Fax 202.408.4400
www.finnegan.com

37. (Currently Amended) ~~The semiconductor device of claim 36,~~ A semiconductor device comprising:

a semiconductor substrate;

a first insulating film formed on said semiconductor substrate;

first conductors formed on said semiconductor substrate through said first insulating film;

first upper wires formed on said first insulating film and said first conductors alternated on two parallel lines such that ends of said first upper wires on one of the parallel lines oppose ends of said first upper wires on the other of the parallel lines; and

a second insulating film formed on said first upper wires and over said first insulating film, said second insulating film including a thin area over said first conductors for guiding a laser beam.

wherein said first conductors include first portions formed on said semiconductor substrate and second portions formed on the first portions made of different material from that of the first portions.

38. (Previously Presented) A semiconductor device comprising:

a first insulating film;

first lower wires formed on said first insulating film alternated on two parallel rows such that ends of said first lower wires on one of the parallel rows oppose ends of said first lower wires on the other of the parallel rows;

a second insulating film formed on said first lower wires;

first conductors formed on said first lower wires through said second insulating film;

FINNEGAN
HENDERSON
FARABOW
GARRETT &
DUNNER LLP

1300 I Street, NW
Washington, DC 20005
202.408.4000
Fax 202.408.4400
www.finnegan.com

first upper wires formed parallel with said first lower wires on said second insulating film and said first conductors; and

a third insulating film formed on said first upper wires and over said second insulating film, said third insulating film including a thin area over said first conductors for guiding a laser beam.

39. (Previously Presented) The semiconductor device of claim 38, wherein said first conductors include first portions formed on said first lower wires and second portions formed on the first portions made of different material from that of the first portions.

40. (Previously Presented) The semiconductor device of claim 38, wherein said first lower wires are obliquely below said first upper wires being able to conduct to said first lower wires.

41. (Previously Presented) A semiconductor device comprising:

a first insulating film;

a first lower wire formed on said first insulating film;

a second insulating film formed on said first lower wire;

a first conductor formed on said first lower wire through said second insulating film;

a second conductor formed on said first lower wire through said second insulating film;

a first upper wire formed on said second insulating film and said first conductor;

a second upper wire formed parallel with said first upper wire on said second insulating film and said second conductor; and

FINNEGAN
HENDERSON
FARABOW
GARRETT &
DUNNER LLP

1300 I Street, NW
Washington, DC 20005
202.408.4000
Fax 202.408.4400
www.finnegan.com

a third insulating film formed on said first upper wire and said second upper wire and over said second insulating film, said third insulating film including a thin area over said first conductor and said second conductor for guiding a laser beam.

42. (Previously Presented) The semiconductor device of claim 41, further comprising:

a second lower wire formed parallel with said first lower wire on said first insulating film beneath said second insulating film;

a third conductor formed on said second lower wire below the thin area through said second insulating film;

a fourth conductor formed on said second lower wire below the thin area through said second insulating film;

a third upper wire formed on an extension line of said first upper wire on said second insulating film and said third conductor beneath said third insulating film; and

a fourth upper wire formed on an extension line of said second upper wire on said second insulating film and said fourth conductor beneath said third insulating film.

43. (Previously Presented) The semiconductor device of claim 41, wherein said first conductor includes a first portion formed on said first lower wire and a second portion formed on the first portion made of different material from that of the first portion.

FINNEGAN
HENDERSON
FARABOW
GARRETT &
DUNNER ^{LLP}

1300 I Street, NW
Washington, DC 20005
202.408.4000
Fax 202.408.4400
www.finnegan.com

44. (Previously Presented) The semiconductor device of claim 42, wherein
said first, second, third and fourth upper wires are alternated on two parallel rows such
that ends of said first and second upper wires on one of the parallel rows oppose to ends of said
third and fourth upper wires on the other of the parallel rows.

FINNEGAN
HENDERSON
FARABOW
GARRETT &
DUNNER LLP

1300 I Street, NW
Washington, DC 20005
202.408.4000
Fax 202.408.4400
www.finnegan.com